

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5590HORIZONTAL DEFLECTION OUTPUT FOR SUPER HIGH RESOLUTION
DISPLAY, COLOR TV FOR MULTI-MEDIA & HDTV

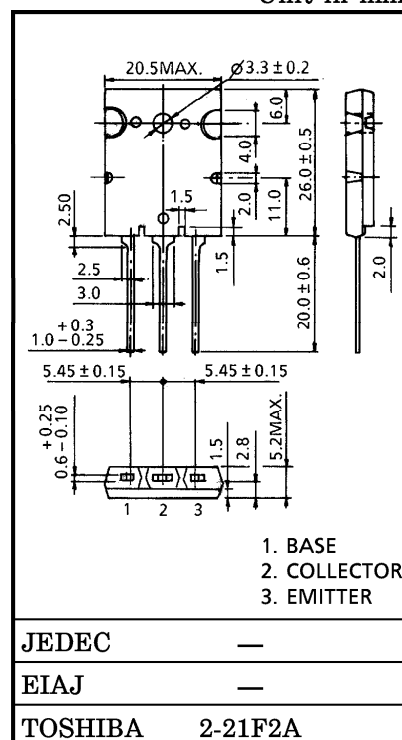
HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CBO} = 1700\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f(2) = 0.1\text{ }\mu\text{s (Typ.)}$

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	1700	V
Collector-Emitter Voltage	V_{CEO}	800	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	DC	I_C	A
	Pulse	I_{CP}	
Base Current	I_B	8	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)	P_C	200	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 150$	$^\circ\text{C}$

Unit in mm



Weight : 9.75 g (Typ.)

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1700\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	800	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 2\text{ A}$	22	—	45	—
		$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 9\text{ A}$	6.5	—	12	
		$h_{FE(3)}$	$V_{CE} = 5\text{ V}, I_C = 12\text{ A}$	4.8	—	8	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 12\text{ A}, I_B = 3\text{ A}$	—	—	3	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 12\text{ A}, I_B = 3\text{ A}$	—	1.0	1.5	V
Transition Frequency		f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	240	—	pF
Switching Time	Storage Time	$t_{stg(1)}$	$I_{CP} = 9\text{ A}, I_{B1}(\text{end}) = 1.1\text{ A}$	—	3.5	4	μs
	Fall Time	$t_f(1)$	$f_H = 32\text{ kHz}$	—	0.25	0.35	
	Storage Time	$t_{stg(2)}$	$I_{CP} = 6.5\text{ A}, I_{B1}(\text{end}) = 1\text{ A}$	—	1.8	2	μs
	Fall Time	$t_f(2)$	$f_H = 100\text{ kHz}$	—	0.1	0.15	

